



Description

The HSM9435 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

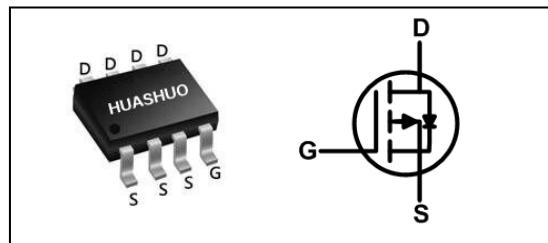
The HSM9435 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-30	V
$R_{DS(ON),max}$	60	mΩ
I_D	-5.5	A

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-5.5	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-4.3	A
I_{DM}	Pulsed Drain Current ²	-20	A
EAS	Single Pulse Avalanche Energy ³	11.3	mJ
I_{AS}	Avalanche Current	15	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	55	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu\text{A}$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BVDSS$ Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=-1\text{mA}$	---	-0.02	---	$\text{V}/^\circ\text{C}$
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-4\text{A}$	---	46	60	$\text{m}\Omega$
		$V_{GS}=-4.5V, I_D=-2\text{A}$	---	65	90	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu\text{A}$	-1.0	---	-2.5	V
$\Delta V_{GS(\text{th})}$	$V_{GS(\text{th})}$ Temperature Coefficient		---	4.32	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	-1	uA
		$V_{DS}=-24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V, I_D=-4\text{A}$	---	5.5	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	24	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V, V_{GS}=-4.5V, I_D=-4\text{A}$	---	5.8	---	nC
Q_{gs}	Gate-Source Charge		---	1.4	---	
Q_{gd}	Gate-Drain Charge		---	2.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega$ $I_D=1\text{A}$	---	18.6	---	ns
T_r	Rise Time		---	12.4	---	
$T_{d(off)}$	Turn-Off Delay Time		---	39.1	---	
T_f	Fall Time		---	5.9	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	483	---	pF
C_{oss}	Output Capacitance		---	89	---	
C_{rss}	Reverse Transfer Capacitance		---	67	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-5.5	A
I_{sM}	Pulsed Source Current ^{2,5}		---	---	-20	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_s=-1\text{A}, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-15\text{A}$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



HUASHUO
SEMICONDUCTOR

HSM9435

Typical Characteristics

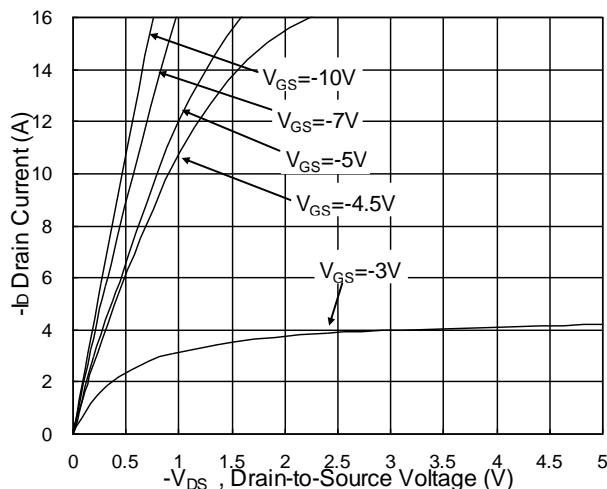


Fig.1 Typical Output Characteristics

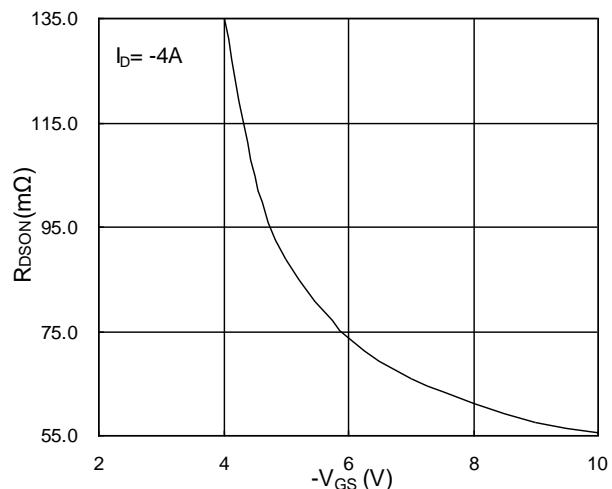


Fig.2 On-Resistance vs. G-S Voltage

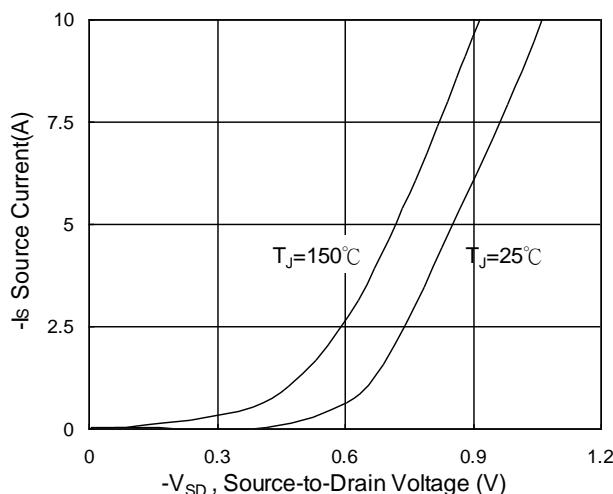


Fig.3 Forward Characteristics of Reverse

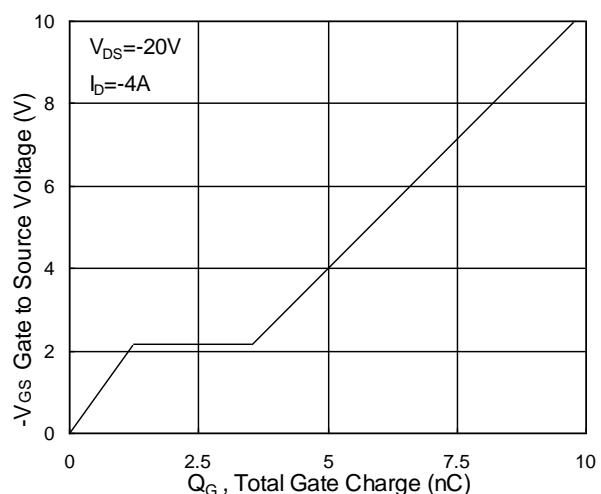


Fig.4 Gate-Charge Characteristics

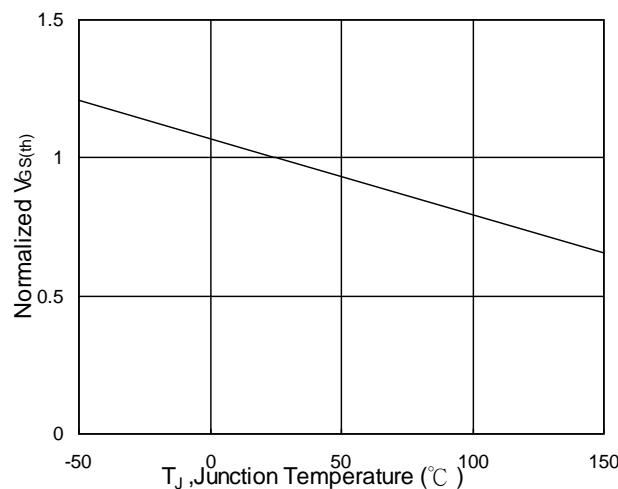


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

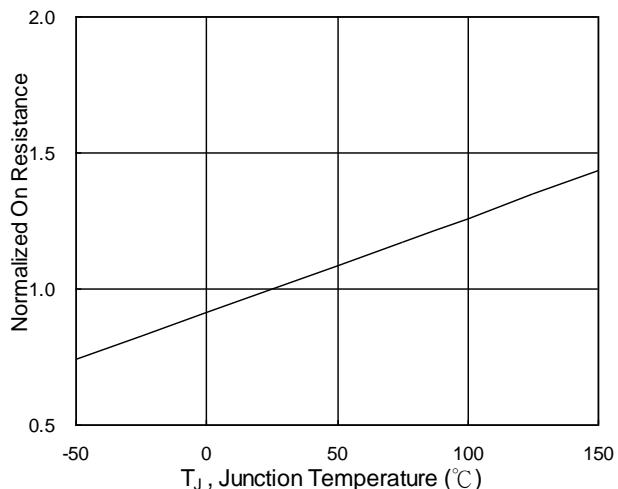


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

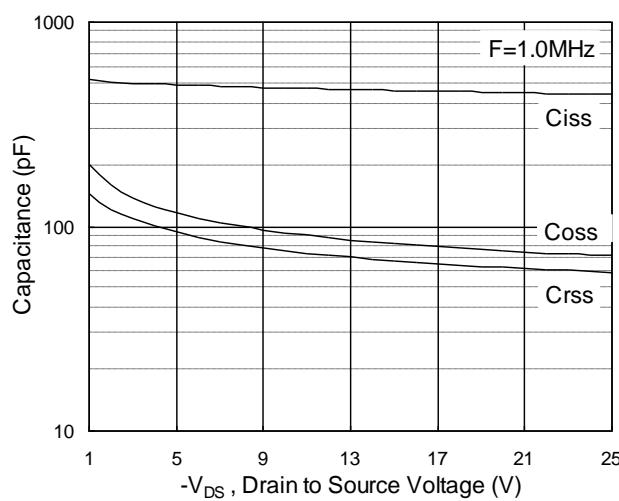


Fig.7 Capacitance

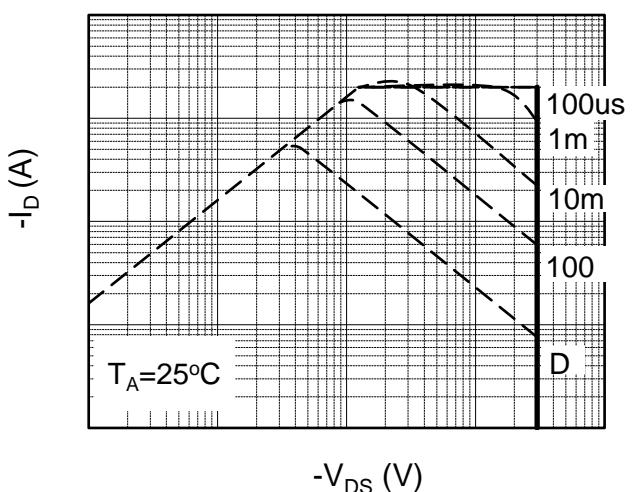


Fig.8 Safe Operating Area

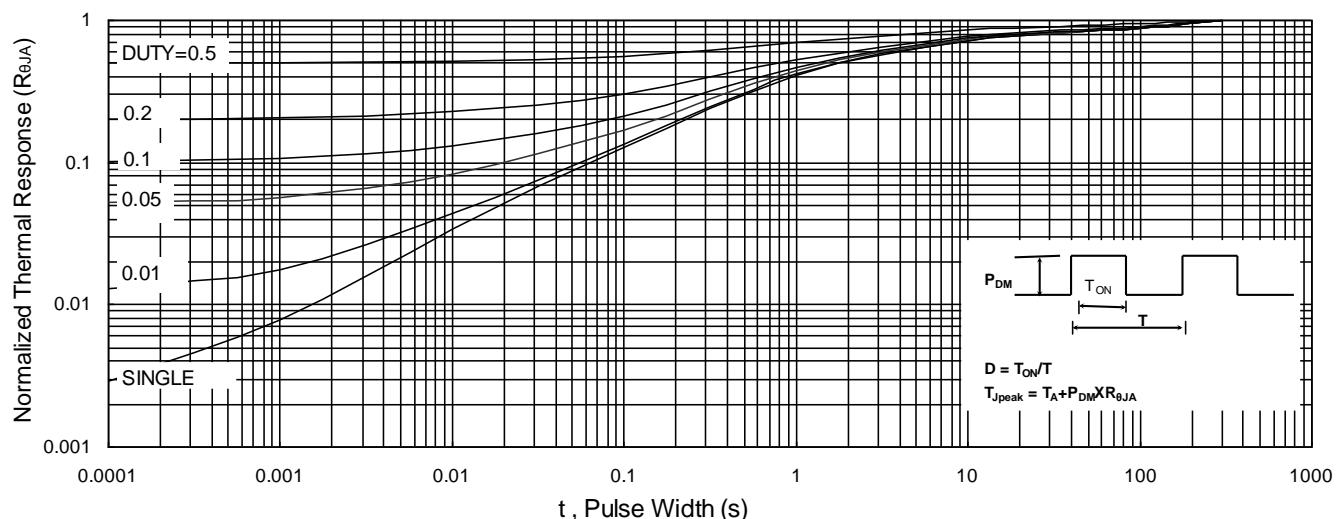


Fig.9 Normalized Maximum Transient Thermal Impedance

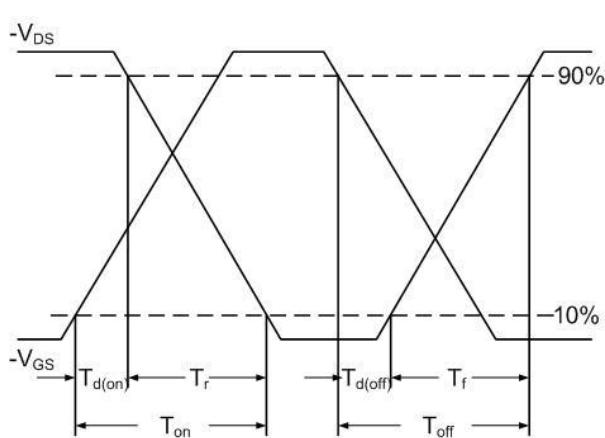


Fig.10 Switching Time Waveform

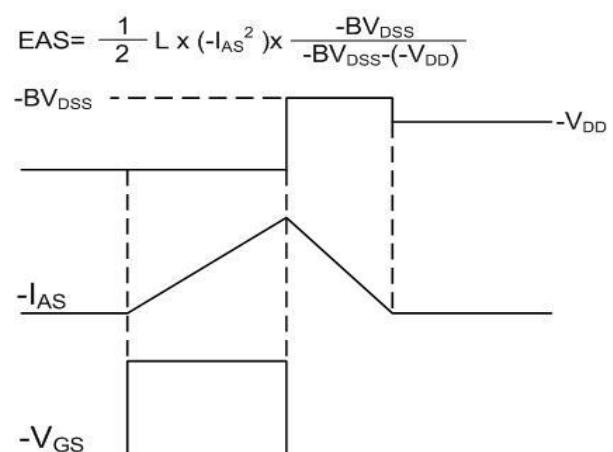


Fig.11 Unclamped Inductive Switching



Ordering Information

Part Number	Package code	Packaging
HSM9435	SOP-8	4000/Tape&Reel

